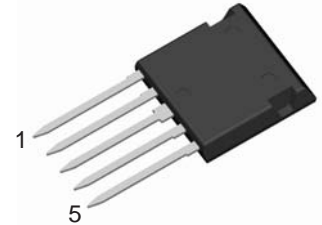
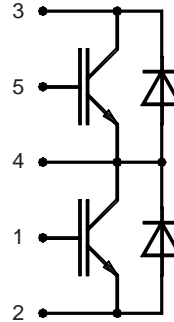


IGBT phaseleg

in ISOPLUS i4-PAC™

FII 40-06D

$I_{C25} = 40 \text{ A}$
 $V_{CES} = 600 \text{ V}$
 $V_{CE(sat) \text{ typ.}} = 1.8 \text{ V}$



IGBTs		
Symbol	Conditions	Maximum Ratings
V_{CES}	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	600 V
V_{GES}		± 20 V
I_{C25}	$T_C = 25^{\circ}\text{C}$	40 A
I_{C90}	$T_C = 90^{\circ}\text{C}$	25 A
I_{CM} V_{CEK}	$V_{GE} = \pm 15 \text{ V}; R_G = 33 \Omega; T_{VJ} = 125^{\circ}\text{C}$ RBSOA, Clamped inductive load; $L = 100 \mu\text{H}$	60 A
		V_{CES}
t_{SC} (SCSOA)	$V_{CE} = V_{CES}; V_{GE} = \pm 15 \text{ V}; R_G = 33 \Omega; T_{VJ} = 125^{\circ}\text{C}$ non-repetitive	10 μs
P_{tot}	$T_C = 25^{\circ}\text{C}$	125 W

Features

- NPT IGBT
 - low saturation voltage
 - positive temperature coefficient for easy paralleling
 - fast switching
- HiPerFRED™ diode
 - optimized fast and soft reverse recovery
 - low operating forward voltage
 - low leakage current
- ISOPLUS i4-PAC™ package
 - isolated back surface
 - enlarged creepage towards heatsink
 - application friendly pinout
 - low inductive current path
 - high reliability
 - industry standard outline

Symbol	Conditions	Characteristic Values ($T_{VJ} = 25^{\circ}\text{C}$, unless otherwise specified)			
		min.	typ.	max.	
$V_{CE(sat)}$	$I_C = 25 \text{ A}; V_{GE} = 15 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		1.8 2.0	V V	
$V_{GE(th)}$	$I_C = 0.7 \text{ mA}; V_{GE} = V_{CE}$	4.5		6.5 V	
I_{CES}	$V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		0.6	0.6 mA mA	
I_{GES}	$V_{CE} = 0 \text{ V}; V_{GE} = \pm 20 \text{ V}$			200 nA	
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 300 \text{ V}; I_C = 25 \text{ A}$ $V_{GE} = \pm 15 \text{ V}; R_G = 33 \Omega$		50 50 270 40	ns ns ns ns	
E_{on}			1.2	mJ	
E_{off}			0.8	mJ	
C_{ies}		$V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}; f = 1 \text{ MHz}$		1.6	nF
Q_{Gon}		$V_{CE} = 300 \text{ V}; V_{GE} = 15 \text{ V}; I_C = 30 \text{ A}$		95	nC
R_{thJC} R_{thJH}	with heat transfer paste		2	1 KW KW	

Applications

- single phaseleg
 - buck-boost chopper
- H bridge
 - power supplies
 - induction heating
 - four quadrant DC drives
 - controlled rectifier
- three phase bridge
 - AC drives
 - controlled rectifier

Diodes

Symbol	Conditions	Maximum Ratings	
I_{F25}	$T_C = 25^\circ\text{C}$	30	A
I_{F90}	$T_C = 90^\circ\text{C}$	15	A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V_F	$I_F = 25\text{ A}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	2.5 1.7	2.8	V V
I_{RM} t_{rr}	} $I_F = 15\text{ A}; di_F/dt = -400\text{ A}/\mu\text{s}; T_{VJ} = 125^\circ\text{C}$ $V_R = 300\text{ V}; V_{GE} = 0\text{ V}$	7		A
		50		ns
R_{thJC} R_{thJH}	(per diode) with heat transfer paste	4.6	2.3	KW KW

Component

Symbol	Conditions	Maximum Ratings	
T_{VJ}		-55...+150	$^\circ\text{C}$
T_{stg}		-55...+125	$^\circ\text{C}$
V_{ISOL}	$I_{ISOL} \leq 1\text{ mA}; 50/60\text{ Hz}$	2500	V~
F_C	mounting force with clip	20...120	N

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
d_S, d_A	pin - pin	1.7		mm
d_S, d_A	pin - backside metal	5.5		mm
Weight		9		g

Dimensions in mm (1 mm = 0.0394")
